

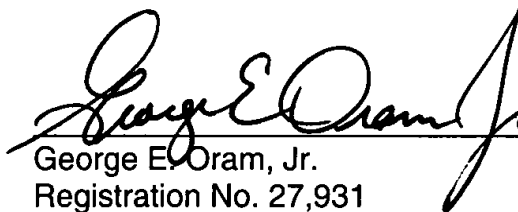
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adjacent layer is 1×10^{15} atoms/cm³ or less and an increment of a boron concentration in a polycrystal silicon adjacent layer of a thickness of 0.5 μ m adjacent to and including an interface between the CVD silicon oxide film and the polycrystal silicon layer relative to a boron concentration in polycrystal silicon in external contact with the polycrystal silicon adjacent layer is 1×10^{15} atoms/cm³ or less. --

REMARKS

Claims 1 - 26 are being canceled and claims 27 - 77 are being added in their place. By this Amendment, the claims are rewritten to delete any multiple dependency. No new matter is contained in the amendments since the claims are merely the written out equivalents of claims 1 - 26.

Please charge any fee deficiency or credit any overpayment to Deposit Account No. 01-2300.

Respectfully submitted,


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